bq2947 具有外部延迟电容器适用于 2 节至 4 节串联锂离子电池的过压保护

1 特性

- 2、3 和 4 节串联电池过压保护
- 外部电容器编程的延迟定时器
- 厂家设定的过压保护 (OVP) 阈值（阈值电压 3.85V 至 4.6V）
- 输出选项：高电平有效或开漏低电平有效
- 高精度过压保护：±10mV
- 低功耗 $I_{CC} \approx 1\mu A$ ($V_{CELL(ALL)} < V_{PROTECT}$)
- 每节电池输入的低泄漏电流 < 100nA
- 小型封装尺寸
  - 8 引脚 WSON (2.00mm x 2.00mm)

2 应用

- 笔记本电脑
- 不间断电源 (UPS) 备用电池

3 说明

bq2947 系列是用于锂离子电池组系统的过压监视器和保护器。独立监控每节电池是否具有过压状态。

在 bq2947 器件中，当检测到任意电池上存在过压状态时，即会启动外部延迟计时器。在延迟定时器超时时，输出被触发进入其激活状态（根据配置的不同为高电平或低电平）。外部延迟定时器的特性还包括检测 CD 引脚上开路或者短路延迟电容器（这也将在过压条件下触发输出驱动器）的功能。

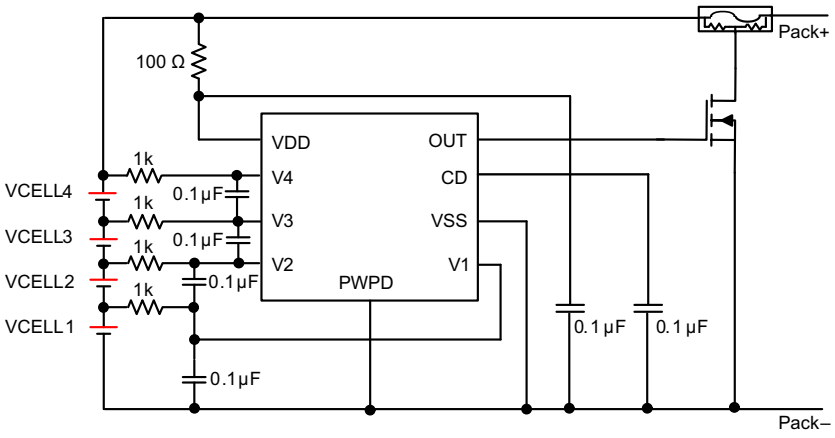
为了实现更快速的产品线测试，bq2947 器件提供具有较短延迟时间的客户测试模式。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
bq294700	WSON (8)	2.00mm x 2.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化原理图



目录

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision H (February 2018) to Revision I **Page**

- Added bq294713 to the *Device Options table* ... 3
- Added bq294713 to the *Electrical Characteristics* ... 5

Changes from Revision G (November 2017) to Revision H **Page**

- Changed bq294712 to Production Data in the *Device Options table* ... 3

Changes from Revision F (January 2017) to Revision G **Page**

- Deleted bq294709 from the *Device Options table* ... 3
- Added bq294712 to the *Device Options table* ... 3
- Added bq294712 and deleted bq294709 in *Electrical Characteristics* ... 5

Changes from Revision E (February 2016) to Revision F **Page**

- Added bq294711 to the *Device Options table* ... 3
- 已添加 *接收文档更新通知* ... 16

Changes from Revision D (November 2015) to Revision E **Page**

- Changed bq297406 device status From: Product Preview To: Active in the *Device Options table* ... 3

Changes from Revision C (November 2015) to Revision D **Page**

- 将器件编号更改为 bq2947 ... 1
- 已将 *相关链接* 表从 *器件和文档支持* 部分中删除 ... 16

Changes from Revision B (August 2014) to Revision C **Page**

- Added preview footnote to the *Device Options table* 3
- Added bq294708 to the *Device Options table* 3

Changes from Revision A (June 2013) to Revision B **Page**

- 已添加 添加了 *ESD 额定值* 表、*特性* 说明部分、*器件功能模式*、*应用和实施*部分、*电源相关建议*部分、*布局*部分、*器件和文档支持*部分以及*机械、封装和可订购信息*部分 1

Changes from Original (September 2012) to Revision A **Page**

- 已添加 向生产数据添加了 bq294707 器件 1

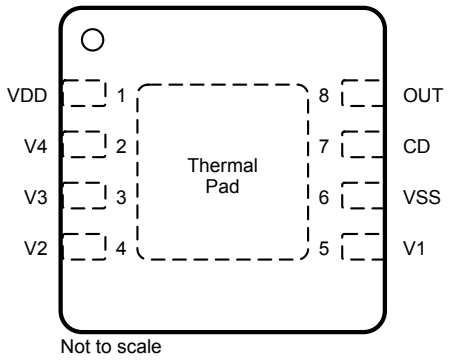
5 Device Options

PART NUMBER	OVP (V)	OV HYSTERESIS	OUTPUT DRIVE
bq294700	4.350	0.300	CMOS Active High
bq294701	4.250	0.300	CMOS Active High
bq294702	4.300	0.300	CMOS Active High
bq294703	4.325	0.300	CMOS Active High
bq294704	4.400	0.300	CMOS Active High
bq294705	4.450	0.300	CMOS Active High
bq294706	4.550	0.300	CMOS Active High
bq294707	4.225	0.050	NCH Open Drain Active Low
bq294708	4.500	0.300	CMOS Active High
bq294711	4.220	0.300	CMOS Active High
bq294712(1)	4.125	0.300	CMOS Active High
bq294713(1)	4.600	0.300	CMOS Active High
bq2947	3.850–4.60	0–0.300	CMOS Active High or Open Drain Active Low

(1) Contact TI for more information.

6 Pin Configuration and Functions

DSG Package
8-Pin WSON
Top View



Not to scale

Pin Functions

NUMBER	NAME	TYPE	DESCRIPTION
1	VDD	P	Power supply input
2	V4	IA	Sense input for positive voltage of the fourth cell from the bottom of the stack
3	V3	IA	Sense input for positive voltage of the third cell from the bottom of the stack
4	V2	IA	Sense input for positive voltage of the second cell from the bottom of the stack
5	V1	IA	Sense input for positive voltage of the lowest cell in the stack
6	VSS	P	Electrically connected to IC ground and negative terminal of the lowest cell in the stack
7	CD	OA(1)	External capacitor connection for delay timer
8	OUT	OA	Analog Output drive for overvoltage fault signal. Active High or Open Drain Active Low
PowerPAD™		P	TI recommends connecting the exposed pad to VSS on the PCB.

(1) IA = Input Analog, OA = Output Analog, P = Power Connection

7 Specifications

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage	VDD–VSS	–0.3	30	V
Input voltage	V4–V3, V3–V2, V2–V1, V1–VSS, or CD–VSS	–0.3	30	V
Output voltage	OUT–VSS	–0.3	30	V
Continuous total power dissipation, P_{TOT}		See *Thermal Information*		
Lead temperature (soldering, 10 s), T_{SOLDER}			300	°C
Storage temperature, T_{stg}		–65	150	

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

Over-operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
Supply voltage, V_{DD}	3	20	V
Input voltage range V4–V3, V3–V2, V2–V1, V1–VSS, or CD–VSS	0	5	V
Operating ambient temperature range, T_A	–40	110	°C

7.4 Thermal Information

THERMAL METRIC(1)		bq2947 WSON 8 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	62	°C/W
$R_{\theta JC(top)}$	Junction-to-case(top) thermal resistance	72	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	32.5	°C/W
ψ_{JT}	Junction-to-top characterization parameter	1.6	°C/W
ψ_{JB}	Junction-to-board characterization parameter	33	°C/W
$R_{\theta JC(bottom)}$	Junction-to-case(bottom) thermal resistance	10	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

7.5 Electrical Characteristics

Typical values stated where T_A = 25°C and VDD = 14.4 V, MIN/MAX values stated where T_A = –40°C to +110°C and V_{DD} = 3 V to 20 V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VOLTAGE PROTECTION THRESHOLDS						
V_{OV}	$V_{(PROTECT)}$ Overvoltage Detection	bq294700, R_{IN} = 1 kΩ		4.350		V
		bq294701, R_{IN} = 1 kΩ		4.250		V
		bq294702, R_{IN} = 1 kΩ		4.300		V
		bq294703, R_{IN} = 1 kΩ		4.325		V
		bq294704, R_{IN} = 1 kΩ		4.400		V
		bq294705, R_{IN} = 1 kΩ		4.450		V
		bq294706, R_{IN} = 1 kΩ		4.550		V
		bq294707, R_{IN} = 1 kΩ		4.225		V
		bq294708, R_{IN} = 1 kΩ		4.500		V
		bq294711, R_{IN} = 1 kΩ		4.220		V
		bq294712(1), R_{IN} = 1 kΩ		4.125		V
		bq294713(1), R_{IN} = 1 kΩ		4.600		V
V_{HYS}	OV Detection Hysteresis	bq2947(2)	250	300	400	mV
V_{OA}	OV Detection Accuracy	T_A = 25°C	–10		10	mV
$V_{OADRIFT}$	OV Detection Accuracy Across Temperature	T_A = –40°C	–40		40	mV
		T_A = 0°C	–20		20	mV
		T_A = 60°C	–24		24	mV
		T_A = 110°C	–54		54	mV
SUPPLY AND LEAKAGE CURRENT						
I_{DD}	Supply Current	(V4–V3) = (V3–V2) = (V2–V1) = (V1–VSS) = 4.0 V at T_A = 25°C (See Figure 10.)		1	2	µA
I_{IN}	Input Current at Vx Pins	(V4–V3) = (V3–V2) = (V2–V1) = (V1–VSS) = 4.0 V at T_A = 25°C (See Figure 10.)	–0.1		0.1	µA

(1) Contact TI for more information.
(2) Future option, contact TI.

Electrical Characteristics (continued)

Typical values stated where T_A = 25°C and VDD = 14.4 V, MIN/MAX values stated where T_A = –40°C to +110°C and V_{DD} = 3 V to 20 V (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{CELL}	Input Current (ALL Vx and VDD Input Pins)	Current Consumption at Power down, (V4–V3) = (V3–V2) = (V2–V1) = (V1–VSS) = 2.30 V at T_A = 25°C		1.1		µA
OUTPUT DRIVE OUT, CMOS ACTIVE HIGH VERSIONS ONLY						
V_{OUT}	Output Drive Voltage, Active High	(V4–V3), (V3–V2), (V2–V1), or (V1–VSS) > V_{OV}, VDD = 14.4 V, I_{OH} = 100 µA	6			V
		If three of four cells are short circuited, only one cell remains powered and > V_{OV}, VDD = Vx (cell voltage), I_{OH} = 100 µA		VDD – 0.3		V
		(V4–V3), (V3–V2), (V2–V1), and (V1–VSS) < V_{OV}, VDD = 14.4 V, I_{OL} = 100 µA measured into OUT pin.		250	400	mV
I_{OUTH}	OUT Source Current (during OV)	(V4–V3), (V3–V2), (V2–V1), or (V1–VSS) > V_{OV}, VDD = 14.4 V, OUT = 0 V, measured out of OUT pin.			4.5	mA
I_{OUTL}	OUT Sink Current (no OV)	(V4–V3), (V3–V2), (V2–V1), and (V1–VSS) < V_{OV}, VDD = 14.4 V, OUT = VDD, measured into OUT pin .Pull resistor R_{PU} = 5 kΩ to VDD = 14.4 V	0.5		14	mA
OUTPUT DRIVE OUT, CMOS OPEN DRAIN ACTIVE LOW VERSIONS ONLY						
V_{OUT}	Output Drive Voltage, Active High	(V4–V3), (V3–V2), (V2–V1), and (V1–VSS) < V_{OV}, VDD = 14.4 V, I_{OL} = 100 µA measured into OUT pin.		250	400	mV
I_{OUTL}	OUT Sink Current (no OV)	(V4–V3), (V3–V2), (V2–V1), and (V1–VSS) < V_{OV}, VDD = 14.4 V, OUT = VDD, measured into OUT pin. Pull resistor R_{PU} = 5 kΩ to VDD = 14.4 V	0.5		14	mA
I_{OUTLK}	OUT pin leakage	(V4–V3), (V3–V2), (V2–V1), and (V1–VSS) < V_{OV}, VDD = 14.4 V, OUT = VDD, measured into OUT pin.			100	nA
DELAY TIMER						
t_{CD}	OV Delay Time	C_{CD} = 0.1 µF (see Equation 1)	1	1.5	2	s
t_{CD_GND}	OV Delay Time with CD pin = 0 V	Delay due to C_{CD} capacitor shorted to ground for Customer Test Mode	20		170	ms

7.6 Typical Characteristics

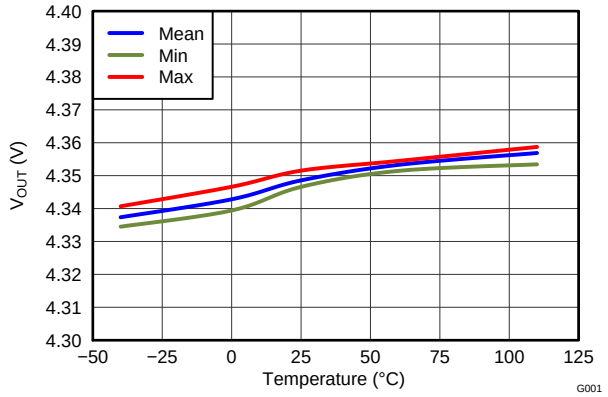


Figure 1. Overvoltage Threshold (Nominal = 4.35 V) vs. Temperature

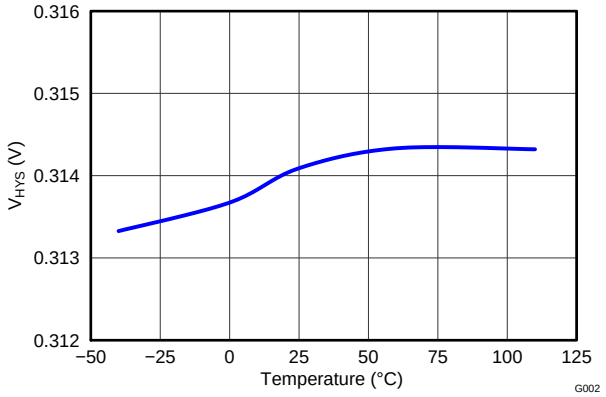


Figure 2. Hysteresis V_{HYS} vs. Temperature

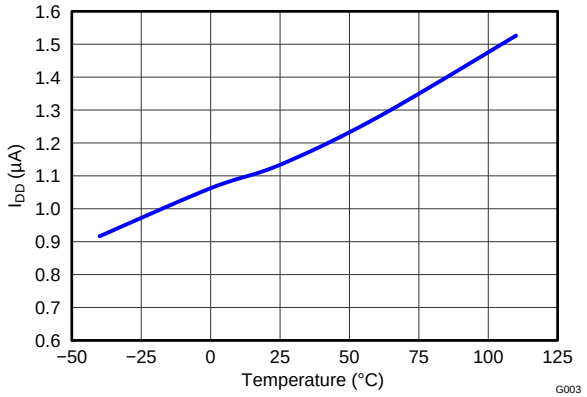


Figure 3. I_{DD} Current Consumption vs. Temperature at VDD = 16 V

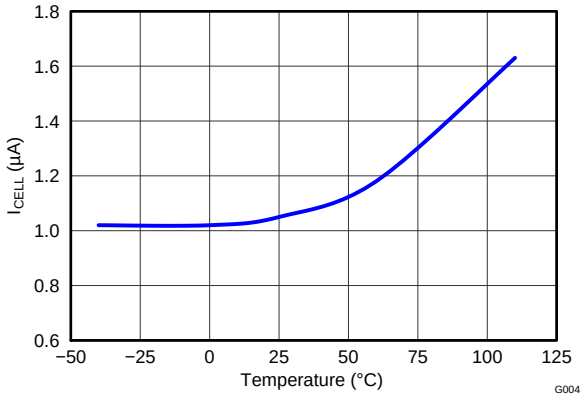


Figure 4. I_{CELL} vs. Temperature at V_{CELL}= 9.2 V

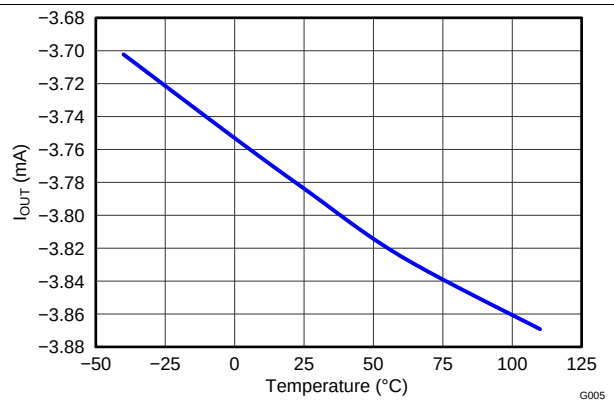


Figure 5. Output Current I_{OUT} vs. Temperature

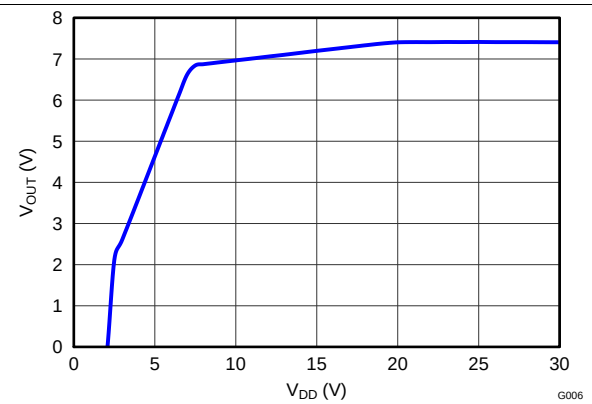


Figure 6. V_{OUT} vs. V_{DD}

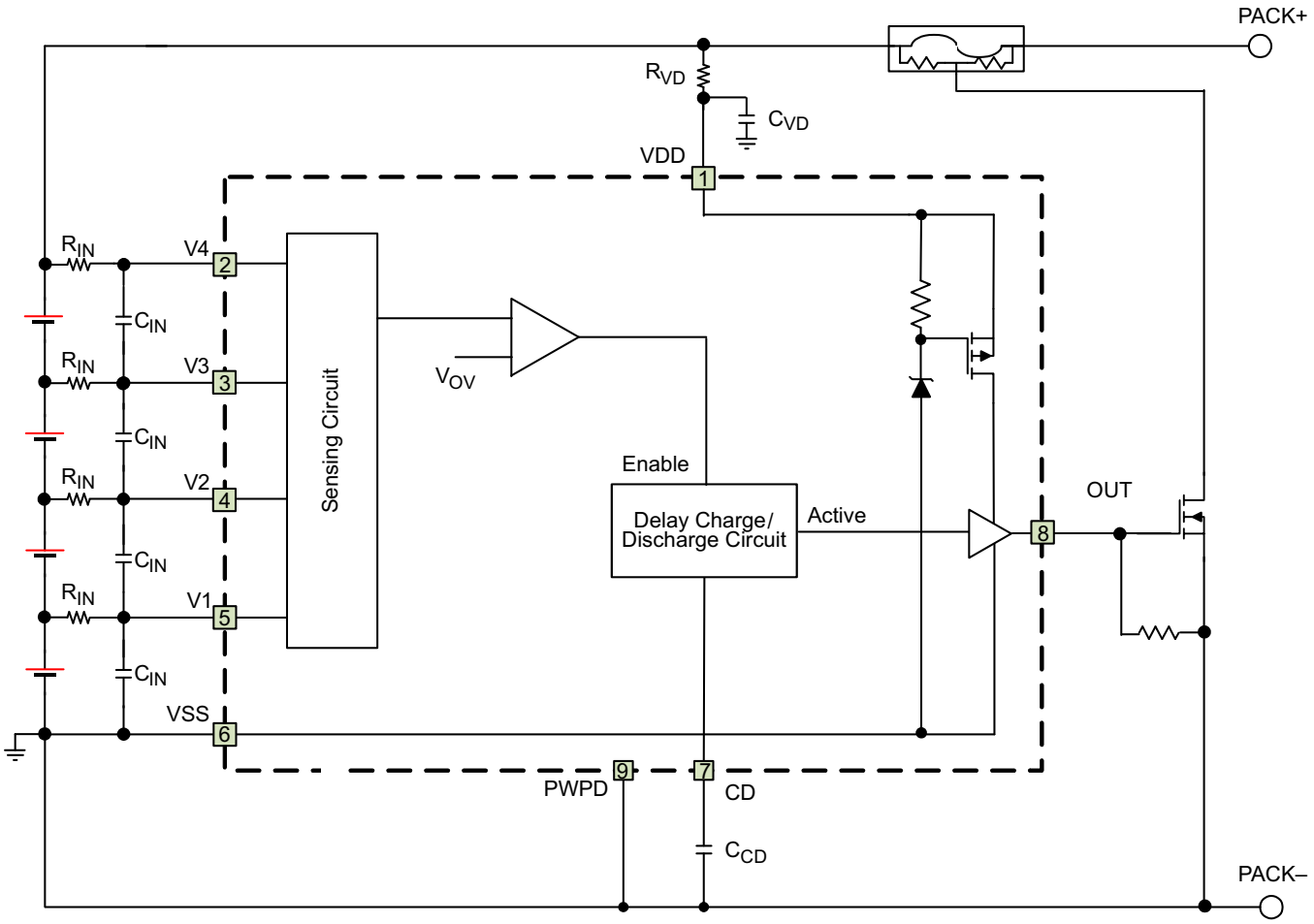
8 Detailed Description

8.1 Overview

The bq2947 is a second level overvoltage (OV) protector. Each cell is monitored independently by comparing the actual cell voltage to a protection voltage threshold, V_{OV}. The protection threshold is preprogrammed at the factory with a range between 3.85 V and 4.65 V.

8.2 Functional Block Diagram

The Functional Block Diagram shows a CMOS Active High configuration.



NOTE

In the case of an Open Drain Active Low configuration, an external pull-up resistor is required on the OUT terminal.

8.3 Feature Description

In the bq2947 family of devices, if any cell voltage exceeds the programmed OV value, a timer circuit is activated. This timer circuit charges the CD pin to a nominal value, then slowly discharges it with a fixed current back down to VSS. When the CD pin falls below a nominal threshold near VSS, the OUT terminal goes from inactive to active state. Additionally, a timeout detection circuit checks to ensure that the CD pin successfully begins charging to above VSS and subsequently drops back down to VSS, and if a timeout error is detected in either direction, it will similarly trigger the OUT pin to become active. See Figure 8 for details on CD and OUT pin behavior during an overvoltage event.

Feature Description (continued)

For an NCH Open Drain Active Low configuration, the OUT pin pulls down to VSS when active (OV present) and is high impedance when inactive (no OV).

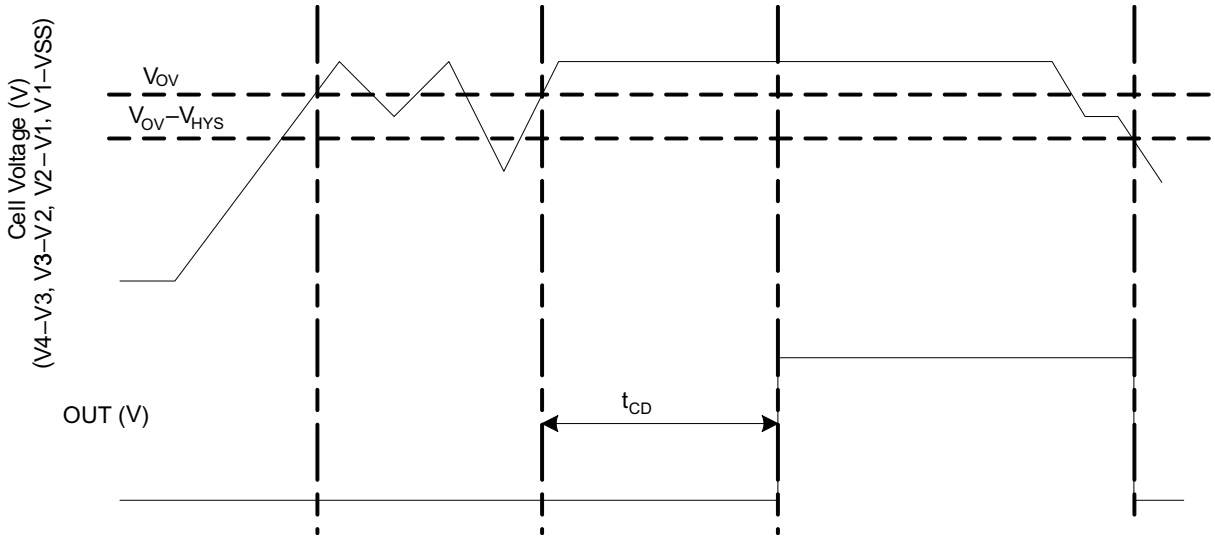


Figure 7. Timing for Overvoltage Sensing (OUT Pin Is Active High)

Figure 8 shows the behavior of CD pin during an OV sequence.

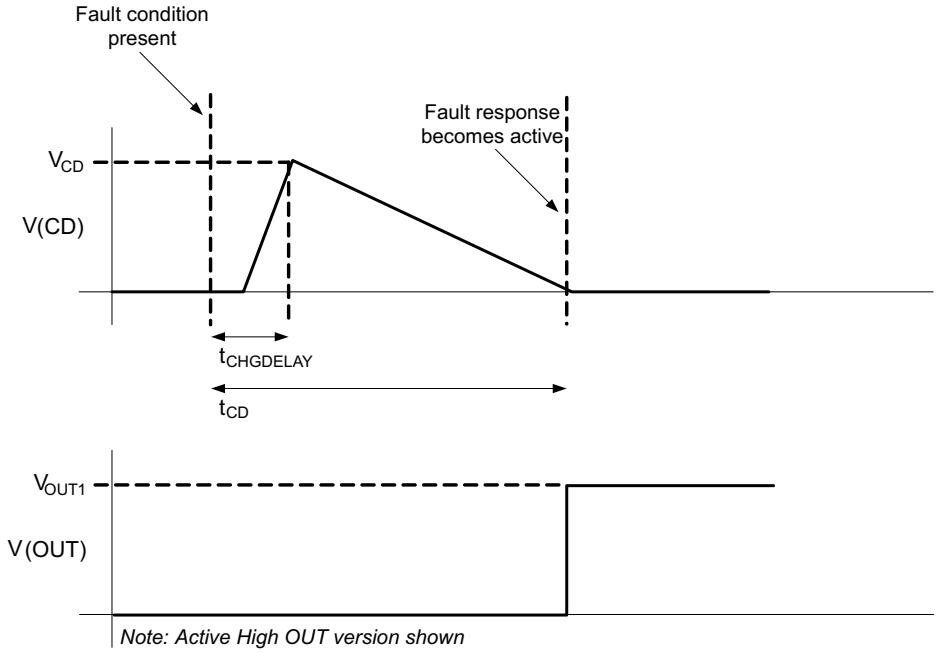


Figure 8. CD Pin Mechanism (OUT Pin Is Active High)

NOTE

In the case of an Open Drain Active Low version, the V_{OUT} signal will be high and transition to low state when the voltage on the V_{CD} capacitor discharges to the set level based on the t_{CD} timer.

Feature Description (continued)

8.3.1 Pin Details

8.3.1.1 Input Sense Voltage, Vx

These inputs sense each battery cell voltage. A series resistor and a capacitor across the cell for each input is required for noise filtering and stable voltage monitoring.

8.3.1.2 Output Drive, OUT

This terminal serves as the fault signal output, and may be ordered in either Active High or Open Drain Active Low options.

8.3.1.3 Supply Input, VDD

This terminal is the unregulated input power source for the IC. A series resistor is connected to limit the current, and a capacitor is connected to ground for noise filtering.

8.3.1.4 External Delay Capacitor, CD

This terminal is connected to an external capacitor that sets the delay timer during an overvoltage fault event.

The CD pin includes a timeout detection circuit to ensure that the output drives active even with a shorted or open capacitor during an overvoltage event.

The capacitor connected on the CD pin rapidly charges to a voltage if any one of the cell inputs exceeds the OV threshold. Then the delay circuit gradually discharges the capacitor on the CD pin. Once this capacitor discharges below a set voltage, the OUT transitions from an inactive to active state.

To calculate the delay, use the following equation:

t_{CD} (sec) = K × C_{CD} (µF), where K = 10 to 20 range. (1)

Example: If C_{CD}= 0.1 µF (typical), then the delay timer range is

t_{CD} (s) = 10 × 0.1 = 1 s (Minimum)

t_{CD} (s) = 20 × 0.1 = 2 s (Maximum)

NOTE

The tolerance on the capacitor used for C_{CD} increases the range of the t_{CD} timer.

8.4 Device Functional Modes

8.4.1 NORMAL Mode

When all of the cell voltages are below the overvoltage threshold, V_{OV}, the device operates in NORMAL mode. The device monitors the differential cell voltages connected across (V1–VSS), (V2–V1), (V3–V2), and (V4–V3). The OUT pin is inactive, and is low if configured active high, or, if configured active low, is an open drain being externally pulled up.

8.4.2 OVERVOLTAGE Mode

OVERVOLTAGE mode is detected if any of the cell voltage exceeds the overvoltage threshold, V_{OV} for configured OV delay time. The OUT pin is activated after a delay time set by the capacitance in the CD pin. The OUT pin will either pull high internally, if configured as active high, or will be pulled low internally if configured as active low. An external FET is then turned on, shorting the fuse to ground, which allows the battery and/or charger power to blow the fuse. When all of the cell voltages fall below the (V_{OV}–V_{HYS}), the device returns to NORMAL mode.

8.4.3 Customer Test Mode

It is possible to reduce test time for checking the overvoltage function by simply shorting the external CD capacitor to VSS. In this case, the OV delay would be reduced to the $t_{(CD\_GND)}$ value, which has a maximum of 170 ms.

Device Functional Modes (continued)

Figure 9 shows the timing for the Customer Test Mode.

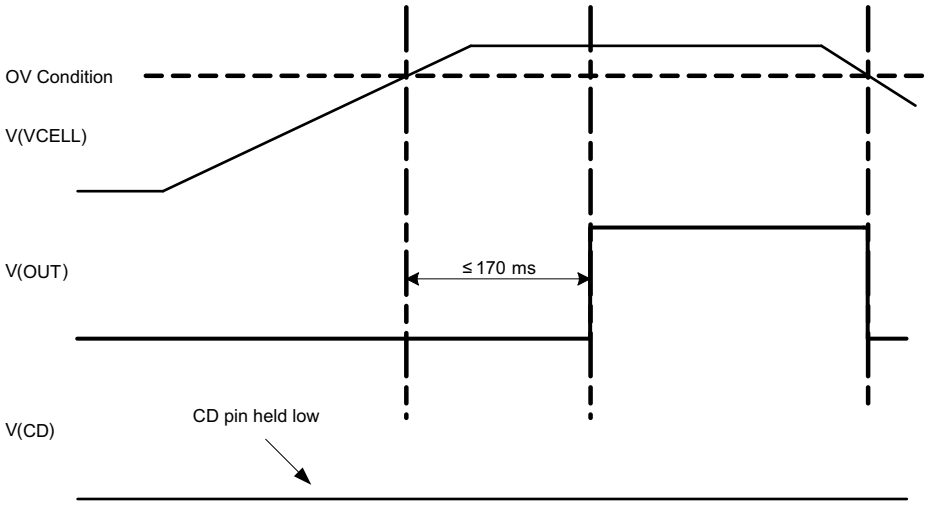
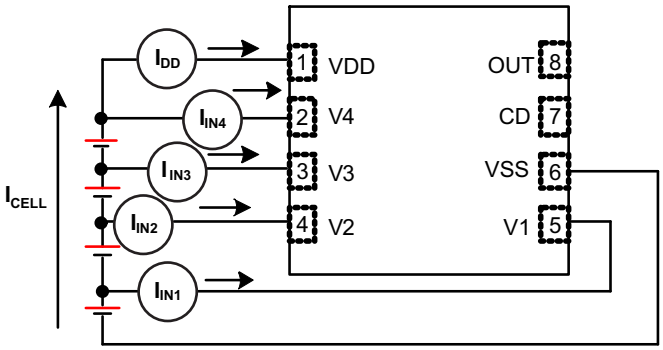


Figure 9. Timing for Customer Test Mode

Figure 10 shows the measurement for current consumption of the product for both VDD and Vx.



$$I_{CELL} = I_{DD} + I_{IN1} + I_{IN2} + I_{IN3} + I_{IN4}$$

Figure 10. Configuration for IC Current Consumption Test

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The bq2947 devices are a family of second-level protectors used for overvoltage protection of the battery pack in the application. The device, when configuring the OUT pin with active high, drives a NMOS FET that connects the fuse to ground in the event of a fault condition. This provides a shorted path to use the battery and/or charger power to blow the fuse and cut the power path. The OUT pin, when configured as active low, can be used to drive a PMOS FET to connect the fuse to ground instead.

9.2 Typical Applications

9.2.1 Application Configuration for Active High

Figure 11 shows the recommended reference design components.

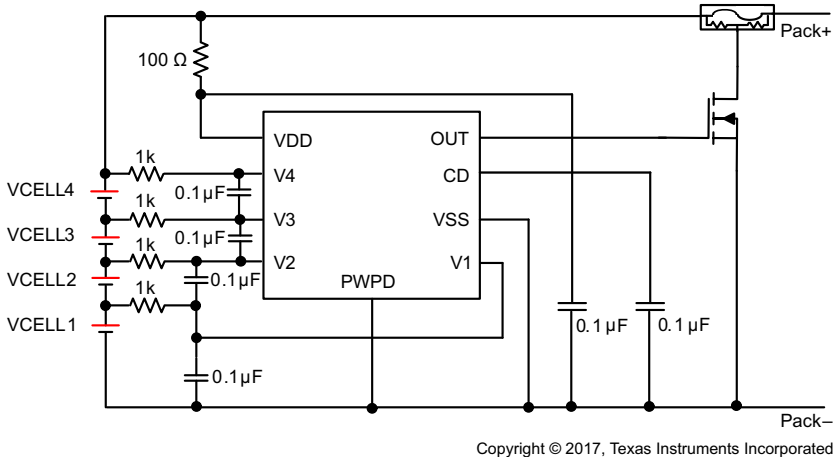


Figure 11. Application Configuration for Active High

9.2.1.1 Design Requirements

NOTE

In the case of an Open Drain Active Low configuration, an external pull-up resistor is required on the OUT terminal.

Changes to the ranges stated in Table 1 will impact the accuracy of the cell measurements.

Table 1. Parameters

PARAMETER	EXTERNAL COMPONENT	MIN	NOM	MAX	UNIT
Voltage monitor filter resistance	R_{IN}	900	1000	4700	Ω
Voltage monitor filter capacitance	C_{IN}	0.01	0.1	1.0	µF
Supply voltage filter resistance	R_{VD}	100		1000	Ω
Supply voltage filter capacitance	C_{VD}		0.1	1.0	µF
CD external delay capacitance	C_{CD}		0.1	1.0	µF

NOTE

The device is calibrated using an R_{IN} value = 1 kΩ. Using a value other than this recommended value changes the accuracy of the cell voltage measurements and V_{OV} trigger level.

9.2.1.2 Detailed Design Procedure

1. Determine the number of cell in series.

   The device supports 2-S to 4-S cell configuration. For 2S and 3S, the top unused pin(s) should be shorted as shown in Figure 12 and Figure 13.

2. Determine the overvoltage protection delay.

   Follow the calculation example described in CD pin description. Select the right capacitor to connect to the CD pin.

3. Follow the application schematic to connect the device. If the OUT pin is configured to open drain, an external pull up resistor should be used.

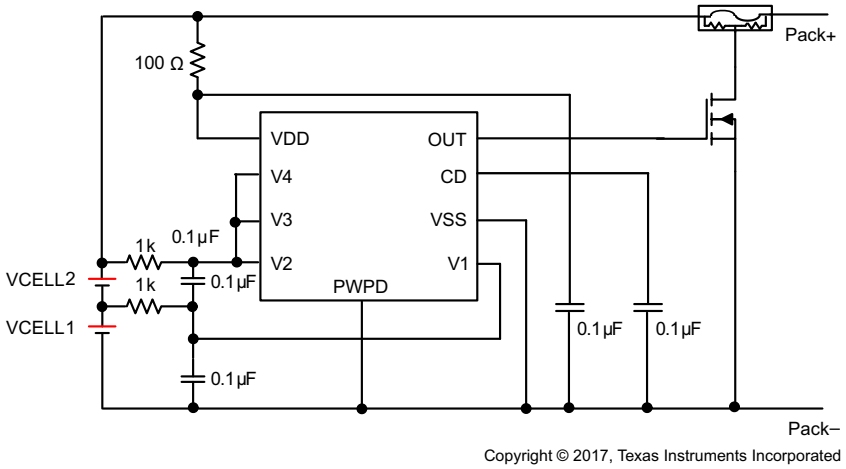


Figure 12. 2-Series Cell Configuration

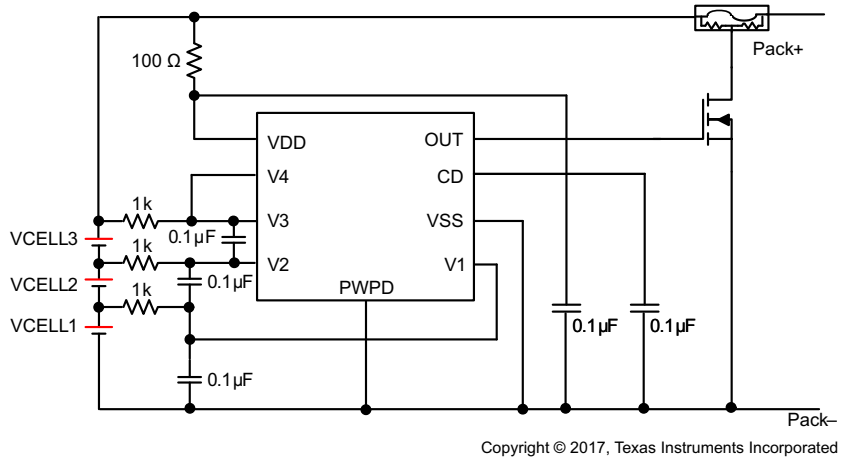


Figure 13. 3-Series Cell Configuration

9.2.1.3 Application Curves

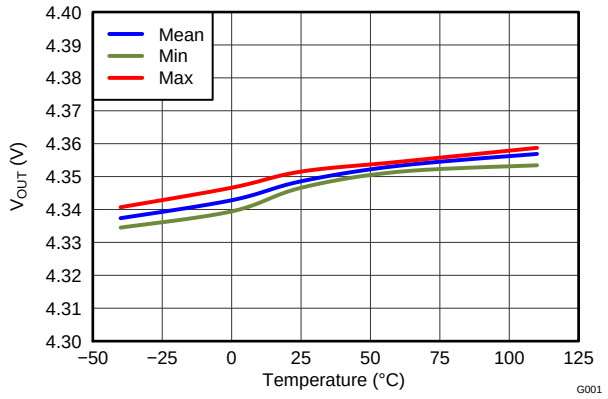


Figure 14. Overvoltage Threshold (OVT) vs. Temperature

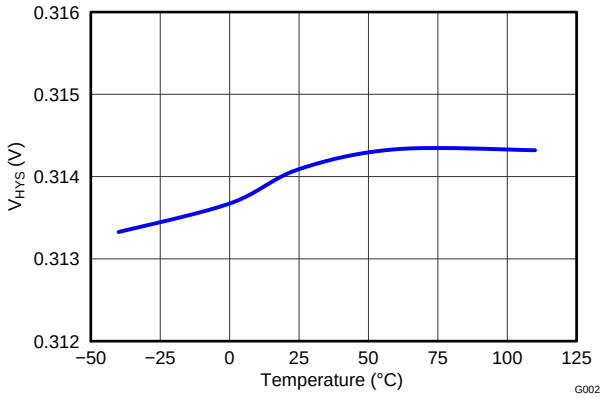


Figure 15. Hysteresis V_{HYS} vs. Temperature

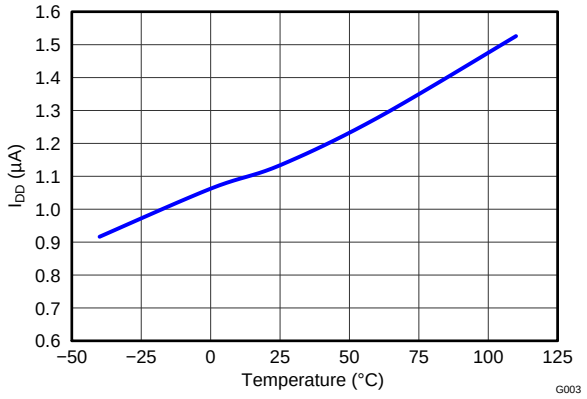


Figure 16. I_{DD} Current Consumption vs. Temperature at VDD = 16 V

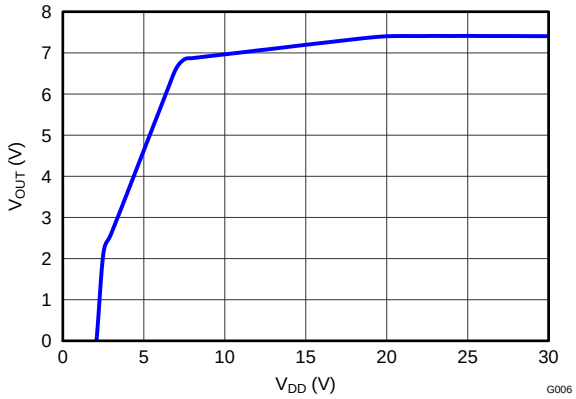


Figure 17. V_{OUT} vs. V_{DD}

10 Power Supply Recommendations

The maximum power of this device is 20 V on V_{DD}.

11 Layout

11.1 Layout Guidelines

1. Ensure the RC filters for the Vx pins and VDD pin are placed as close as possible to the target terminal, reducing the tracing loop area.
2. The capacitor for CD should be placed close to the IC terminals.
3. Ensure the trace connecting the fuse to the gate, source of the NFET to the Pack– is sufficient to withstand the current during fuse blown event.

11.2 Layout Example

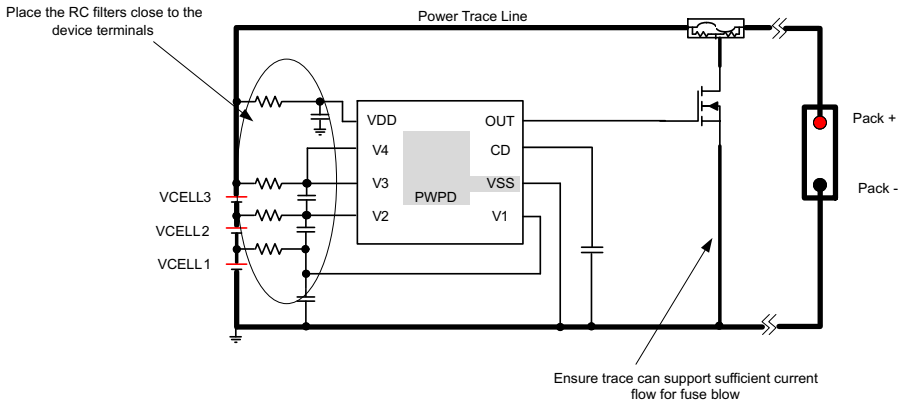


Figure 18. Layout Example

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

如需相关文档，请参阅*《bq2945xy 和 bq2947xy 级联电压监测》*(SLUA662)。

12.2 接收文档更新通知

要接收文档更新通知，请导航至 ti.com.cn 上的器件产品文件夹。单击右上角的*通知我* 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 《使用条款》。

TI E2E™ 在线社区 ***TI 的工程师对工程师 (E2E) 社区。*** **此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。**

设计支持 ***TI 参考设计支持*** **可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。**

12.4 商标

PowerPAD, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 静电放电警告

ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

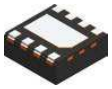
12.6 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此产品说明书的浏览器版本，请查阅左侧的导航栏。

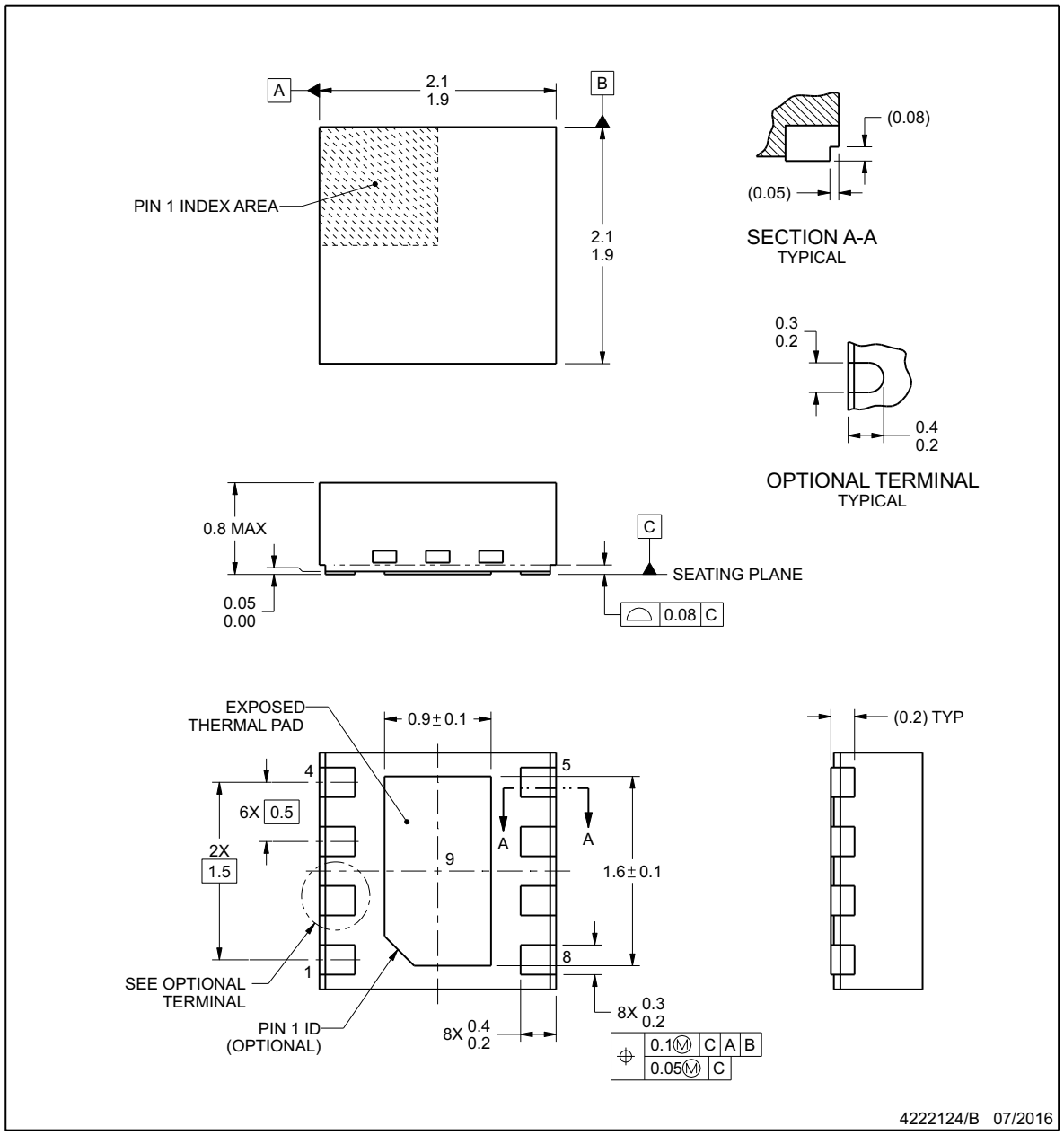


PACKAGE OUTLINE

DSG0008B

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES:

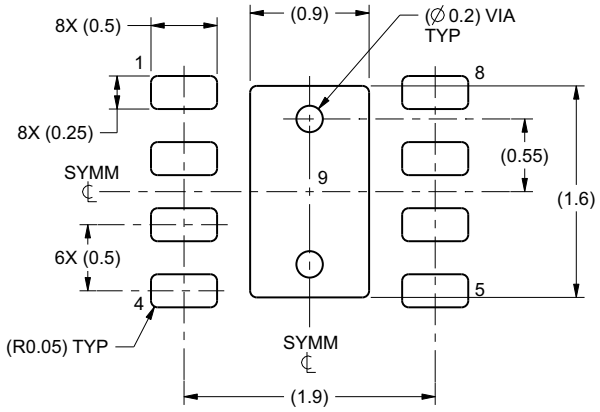
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

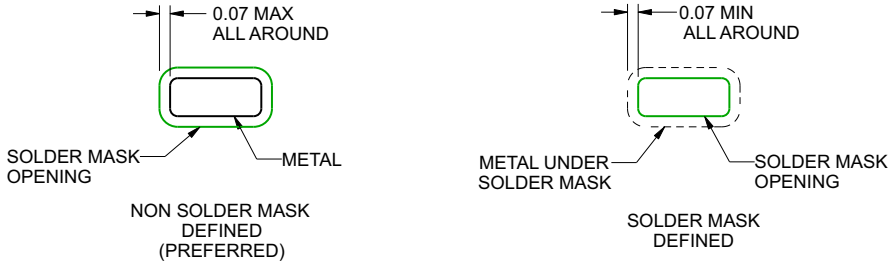
DSG0008B

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
SCALE:20X



SOLDER MASK DETAILS

4222124/B 07/2016

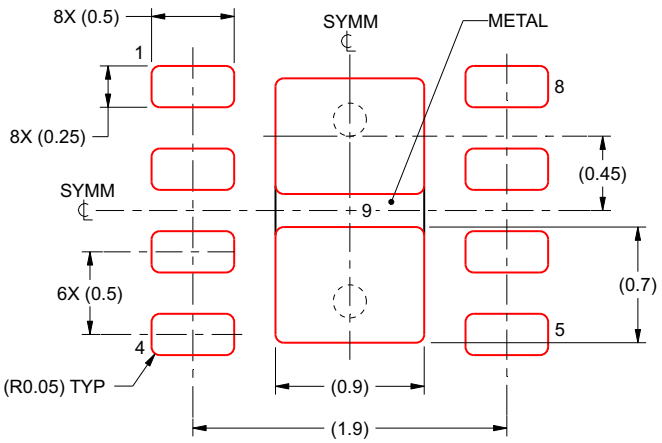
NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DSG0008B — **WSON - 0.8 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

4222124/B 07/2016

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
BQ294700DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	700	Samples
BQ294700DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	700	Samples
BQ294701DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	701	Samples
BQ294701DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	701	Samples
BQ294702DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	702	Samples
BQ294702DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	702	Samples
BQ294703DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	703	Samples
BQ294703DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	703	Samples
BQ294704DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	704	Samples
BQ294704DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	704	Samples
BQ294705DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	705	Samples
BQ294705DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	705	Samples
BQ294706DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	706	Samples
BQ294706DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	706	Samples
BQ294707DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	707	Samples
BQ294707DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	707	Samples
BQ294708DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	Call TI | NIPDAU	Level-2-260C-1 YEAR	-40 to 85	708	Samples
BQ294708DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	Call TI | NIPDAU	Level-2-260C-1 YEAR	-40 to 85	708	Samples
BQ294711DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	711	Samples
BQ294711DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	711	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
BQ294712DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	712	Samples
BQ294712DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	712	Samples
BQ294713DSGR	ACTIVE	WSON	DSG	8	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	713	Samples
BQ294713DSGT	ACTIVE	WSON	DSG	8	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 110	713	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

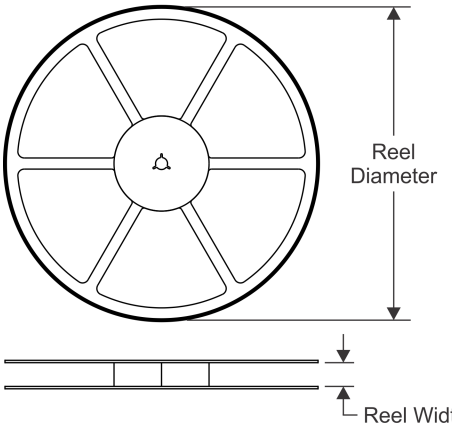
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

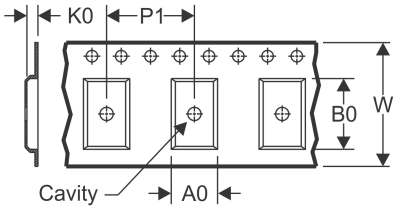
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

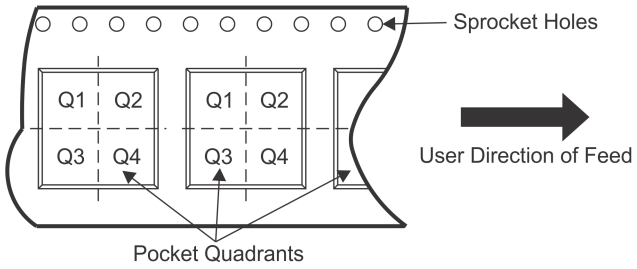


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

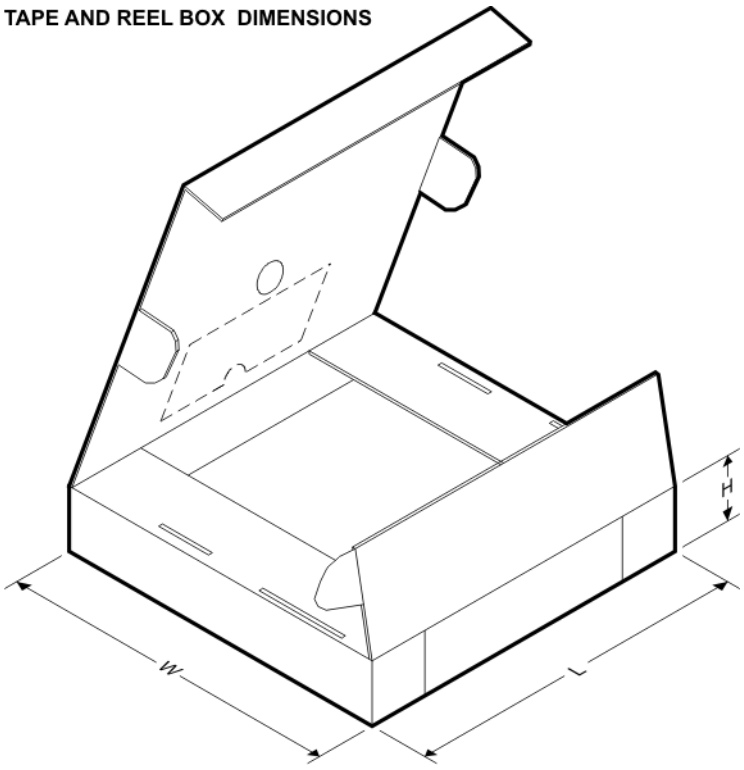


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ294700DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294700DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294701DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294701DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294702DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294702DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294703DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294703DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294704DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294704DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294705DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294705DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294706DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294706DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294707DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294707DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294708DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294708DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ294711DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294711DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294712DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294712DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294712DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294712DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294713DSGR	WSON	DSG	8	3000	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2
BQ294713DSGT	WSON	DSG	8	250	180.0	8.4	2.3	2.3	1.15	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ294700DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294700DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294701DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294701DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294702DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294702DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294703DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294703DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294704DSGR	WSON	DSG	8	3000	210.0	185.0	35.0

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ294704DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294705DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294705DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294706DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294706DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294707DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294707DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294708DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294708DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294711DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294711DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294712DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294712DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294712DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294712DSGT	WSON	DSG	8	250	210.0	185.0	35.0
BQ294713DSGR	WSON	DSG	8	3000	210.0	185.0	35.0
BQ294713DSGT	WSON	DSG	8	250	210.0	185.0	35.0

GENERIC PACKAGE VIEW

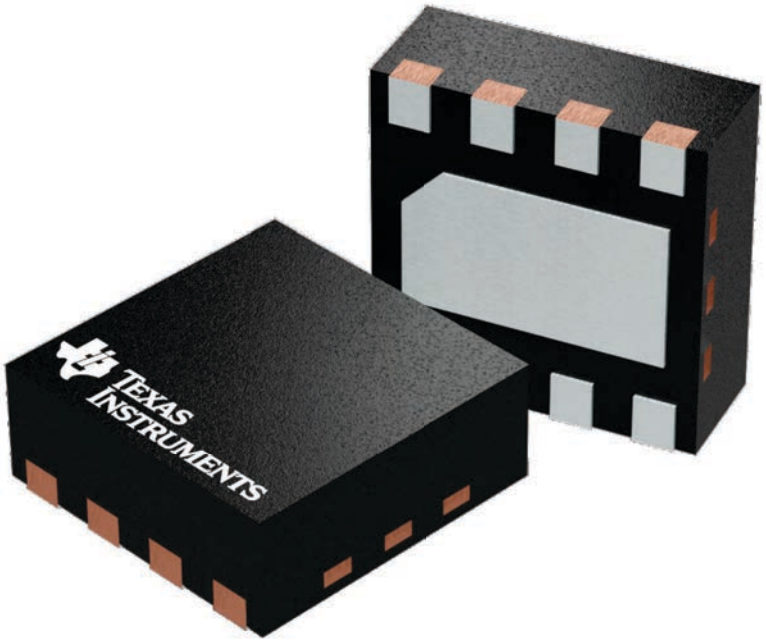
DSG 8

WSON - 0.8 mm max height

2 x 2, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



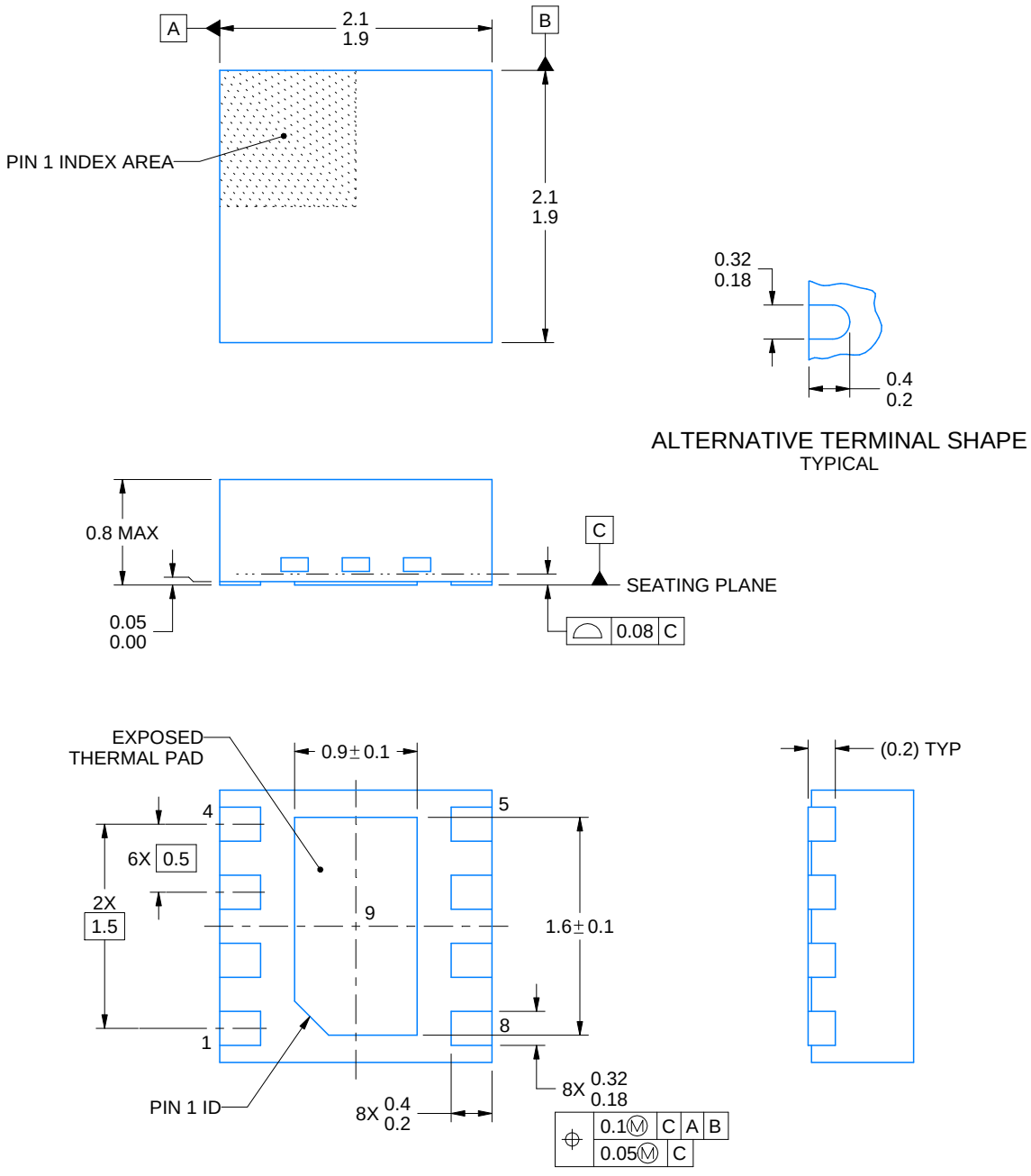
4224783/A

PACKAGE OUTLINE

DSG0008A

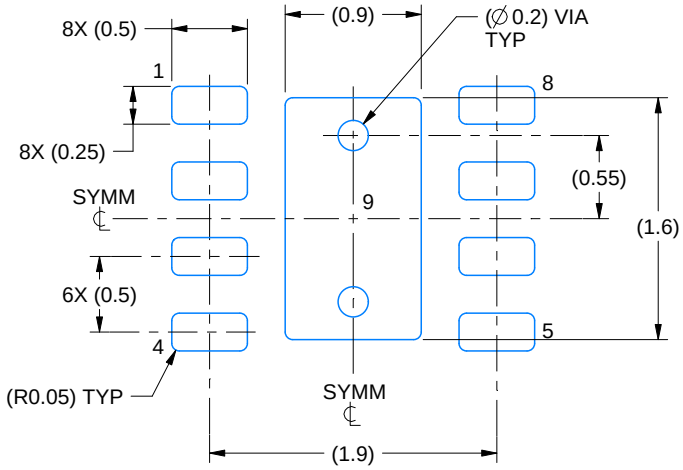
WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

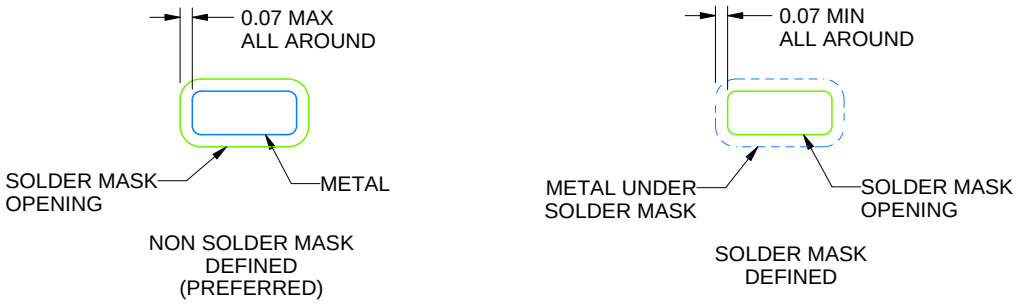


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE:20X



SOLDER MASK DETAILS

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NOTES: (continued)

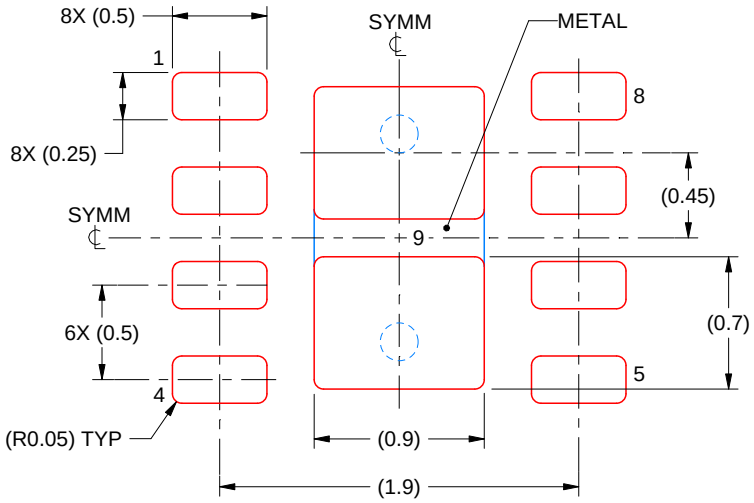
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DSG0008A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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